

# **STEALTH™ Diode** 50 A, 600 V

# FFH50US60S

#### Description

The FFH50US60S is a STEALTH  $^{\text{TM}}$  diode optimized for low loss performance in output rectification. The STEALTH family exhibits low reverse recovery current ( $I_{RR}$ ), low  $V_F$  and soft recovery under typical operating conditions. This device is intended for use as an output rectification diode in Telecom power supplies and other power switching applications. Lower  $V_F$  and  $I_{RR}$  reduces diode losses.

#### **Features**

- Stealth Recovery,  $t_{rr} = 113 \text{ ns}$  (@  $I_F = 50 \text{ A}$ )
- Max Forward Voltage,  $V_F = 1.54 \text{ V}$  (@  $T_C = 25^{\circ}\text{C}$ )
- 600 V Reverse Voltage and High Reliability
- Operating Temperature = 175°C
- Avalanche Energy Rated
- This Device is Pb-Free and is RoHS Compliant

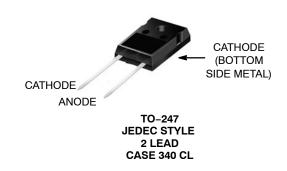
## **Applications**

- SMPS, Welders
- Power Factor Correction
- Uninterruptible Power Supplies
- Motor Drives

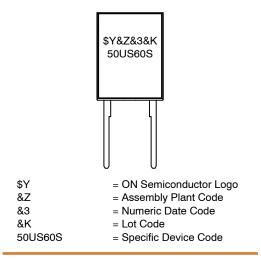
# ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	600	V
Working Peak Reverse Voltage	$V_{RWM}$	600	V
DC Blocking Voltage	V <sub>R</sub>	600	V
Average Rectified Forward Current $(T_C = 120^{\circ}C)$	I <sub>F(AV)</sub>	50	Α
Repetitive Peak Surge Current (20 kHz Square Wave)	I <sub>FRM</sub>	100	Α
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60 Hz)	I <sub>FSM</sub>	500	Α
Power Dissipation	$P_{D}$	200	W
Avalanche Energy (1 A, 40 mH)	E <sub>AVL</sub>	20	mJ
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to 175	°C
Maximum Temperature for Soldering Leads at 0.063 in (1.6 mm) from Case for 10 s	T <sub>L</sub>	300	°C
Maximum Temperature for Soldering Package Body for 10 s	T <sub>PKG</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### **MARKING DIAGRAM**





#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Packing Methode	Reel Size	Tape Width	Quantity
FFH50US60S	FFH50US60S	TO247-2L	Tube	N/A	N/A	30

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test C	Conditions	Min.	Тур.	Max.	Unit
FF STATE CI	HARACTERISTICS	•			•		
I <sub>R</sub>	Instantaneous Reverse Current	V <sub>R</sub> = 600 V	T <sub>C</sub> = 25°C	-	-	100	μΑ
			T <sub>C</sub> = 125°C	_	-	1	mA
N CHARACT	ERISTICS	•			•		•
$V_{F}$	Instantaneous Forward Voltage	I <sub>F</sub> = 50 A	T <sub>C</sub> = 25°C	-	1.38	1.54	V
			T <sub>C</sub> = 125°C	-	1.37	1.53	٧
YNAMIC CHA	ARACTERISTICS	•			•		•
CJ	Junction Capacitance	V <sub>R</sub> = 10 V, I <sub>F</sub> = 0 A		_	110	_	pF
SWITCHING C	HARACTERISTICS	•					
T <sub>rr</sub>	Reverse Recovery Time	$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, V}_R = 15 \text{ V}$		_	47	80	ns
		$I_F = 50 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 15 \text{ V}$		_	75	124	ns
T <sub>rr</sub>	Reverse Recovery Time	$I_F = 50 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 390 \text{ V},$ $T_C = 25^{\circ}\text{C}$		-	113	_	ns
I <sub>RR</sub>	Reverse Recovery Current			-	9.6	-	Α
Q <sub>RR</sub>	Reverse Recovered Charge			-	0.9	-	μС
T <sub>rr</sub>	Reverse Recovery Time	$I_F = 50 \text{ A}, \text{ dIr/dt} = 200 \text{ A/}\mu\text{s}, \text{ V}_R = 390 \text{ V}, \\ T_C = 125^{\circ}\text{C}$		-	235	-	ns
S	Softness Factor (t <sub>b</sub> /t <sub>a</sub> )			-	1.5	-	-
I <sub>RR</sub>	Reverse Recovery Current			-	15	-	Α
Q <sub>RR</sub>	Reverse Recovered Charge			_	2.3	_	μС
T <sub>rr</sub>	Reverse Recovery Time	$I_F = 50 \text{ A}, dI_F/dt =$	1000 A/μs,	-	110	-	ns
S	Softness Factor (t <sub>b</sub> /t <sub>a</sub> )	$V_R = 390 \text{ V}, T_C =$	V <sub>R</sub> = 390 V, T <sub>C</sub> = 125°C		0.8	-	-
I <sub>RR</sub>	Reverse Recovery Current			-	46	-	Α
Q <sub>RR</sub>	Reverse Recovered Charge			-	3.1	-	μС
dl <sub>M</sub> /dt	Maximum di/dt during t <sub>b</sub>			ı	1000	-	A/μs
HERMAL CH	ARACTERISTICS						
$R_{ hetaJC}$	Thermal Resistance Junction to Case			-	-	0.75	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-247		-	-	30	°C/W

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **TYPICAL PERFORMANCE CURVES**

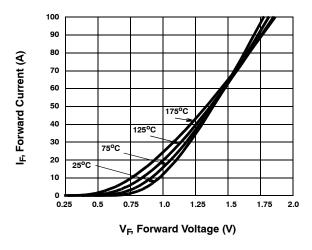


Figure 1. Forward Current vs. Forward Voltage

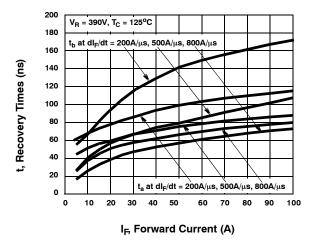


Figure 3. t<sub>a</sub> and t<sub>b</sub> Curves vs. Forward Current

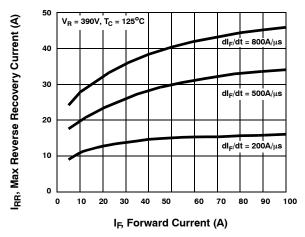


Figure 5. Maximum Reverse Recovery Current vs. Forward Current

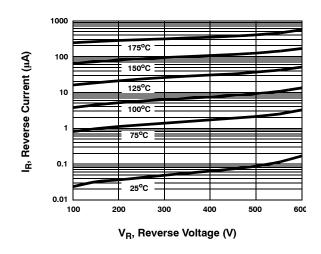


Figure 2. Reverse Current vs. Reverse Voltage

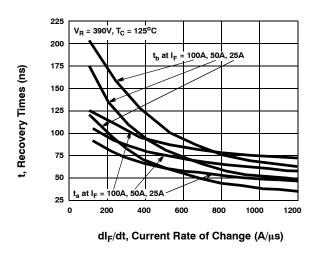


Figure 4. t<sub>a</sub> and t<sub>b</sub> Curves vs. dl<sub>F</sub>/dt

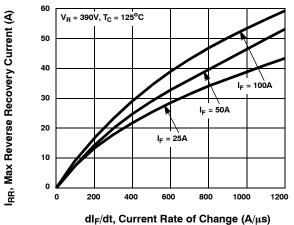


Figure 6. Maximum Reverse Recovery Current vs. dl<sub>F</sub>/dt

# **TYPICAL PERFORMANCE CURVES**

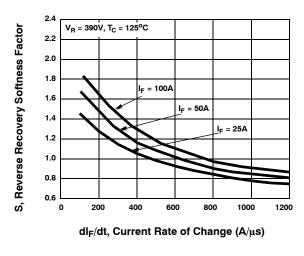


Figure 7. Reverse Recovery Softness Factor vs. dl<sub>F</sub>/dt

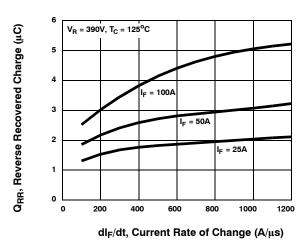


Figure 8. Reverse Recovery Charge vs. dl<sub>F</sub>/dt

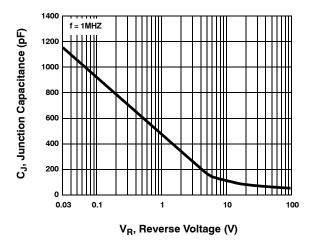


Figure 9. Junction Capacitance vs. Reverse Voltage

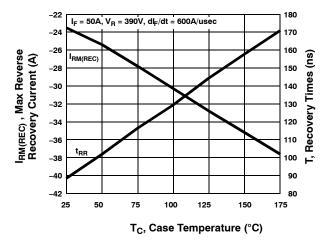


Figure 10. Maximum Reverse Recovery Current and t<sub>rr</sub> vs. Case Temperature

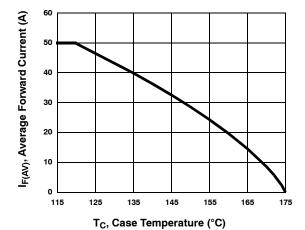


Figure 11. DC Current Derating Curve

#### **TYPICAL PERFORMANCE CURVES**

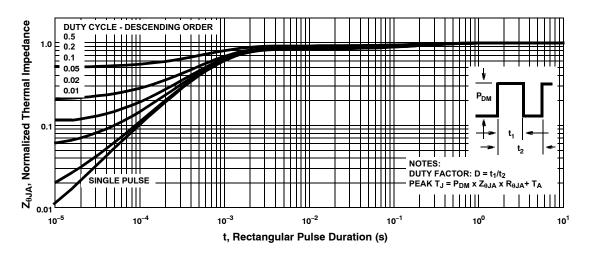


Figure 12. Normalized Maximum Transient Thermal Impedance

# **TEST CIRCUITS AND WAVEFORMS**

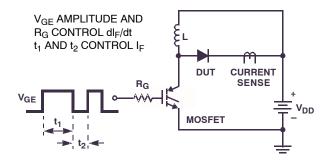


Figure 13. T<sub>rr</sub> Test Circuit

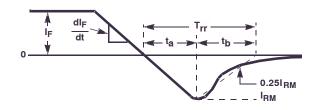


Figure 14. T<sub>rr</sub> Waveforms and Definitions

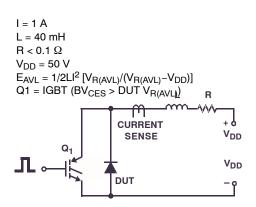


Figure 15. Avalanche Energy Test Circuit

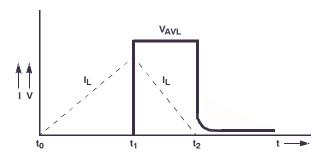
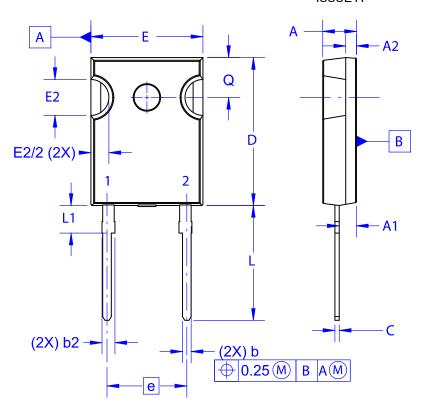


Figure 16. Avalanche Current and Voltage Waveforms

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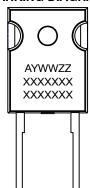
# TO-247-2LD CASE 340CL **ISSUE A**





- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
  D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

# **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code

= Assembly Location

= Year

WW = Work Week

= Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

	DATE 03 DEC 2019		
Ø P —		Ø P1 D2	
E1 —	1	D1	
,		9	

DIM	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A1	2.29	2.40	2.66	
A2	1.30	1.50	1.70	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	16.37	16.57	16.77	
D2	0.51	0.93	1.35	
Е	15.37	15.62	15.87	
E1	12.81	l	~	
E2	4.96	5.08	5.20	
е	~	11.12	~	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØΡ	3.51	3.58	3.65	
Ø <b>P</b> 1	6.61	6.73	6.85	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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